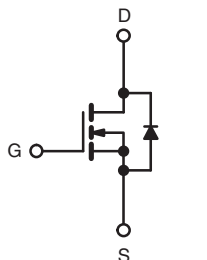
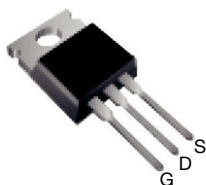


## E Series Power MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	650	
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	$V_{GS} = 10$ V	0.28
$Q_g$ max. (nC)	78	
$Q_{gs}$ (nC)	9	
$Q_{gd}$ (nC)	17	
Configuration	Single	

**TO-220AB**


N-Channel MOSFET

### FEATURES

- Low Figure-of-Merit (FOM)  $R_{on} \times Q_g$
- Low Input Capacitance ( $C_{iss}$ )
- Reduced Switching and Conduction Losses
- Ultra Low Gate Charge ( $Q_g$ )
- Avalanche Energy Rated (UIS)
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Server and Telecom Power Supplies
- Switch Mode Power Supplies (SMPS)
- Power Factor Correction Power Supplies (PFC)
- Lighting
  - High-Intensity Discharge (HID)
  - Fluorescent Ballast Lighting
- Industrial
  - Welding
  - Induction Heating
  - Motor Drives
  - Battery Chargers
  - Renewable Energy
  - Solar (PV Inverters)

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	SiHP15N60E-E3
Lead (Pb)-free and Halogen-free	SiHP15N60E-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Gate-Source Voltage AC ( $f > 1$ Hz)		30	
Continuous Drain Current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	39	
Linear Derating Factor		1.4	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	102	mJ
Maximum Power Dissipation	$P_D$	180	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150	°C
Drain-Source Voltage Slope	$dV/dt$	37	V/ns
Reverse Diode $dV/dt$ <sup>d</sup>		7.7	
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s	300	°C


#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 11.6$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 4.2$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C.

**THERMAL RESISTANCE RATINGS**

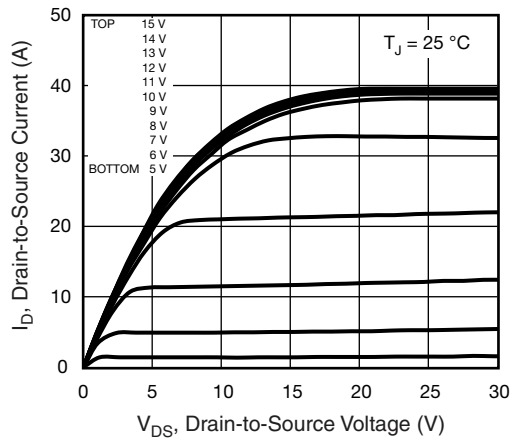
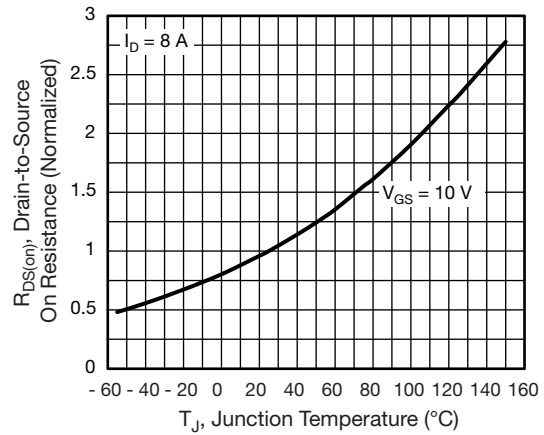
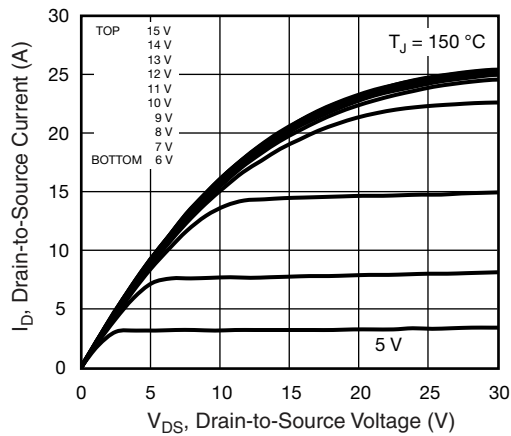
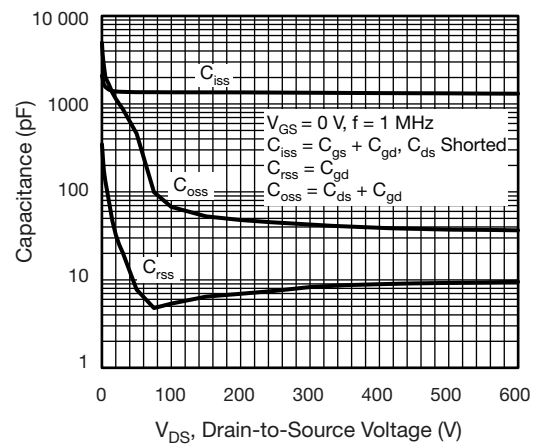
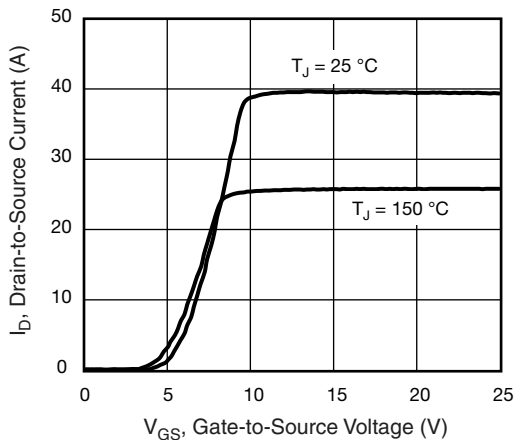
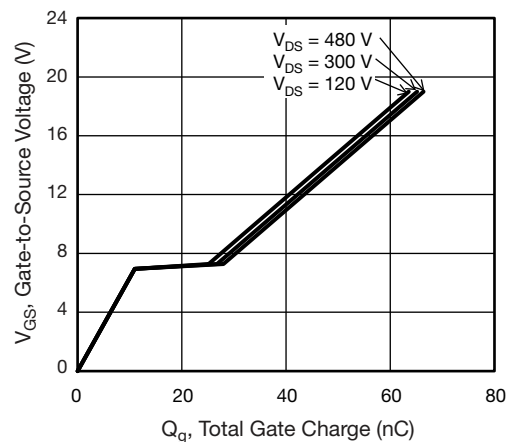
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.7	

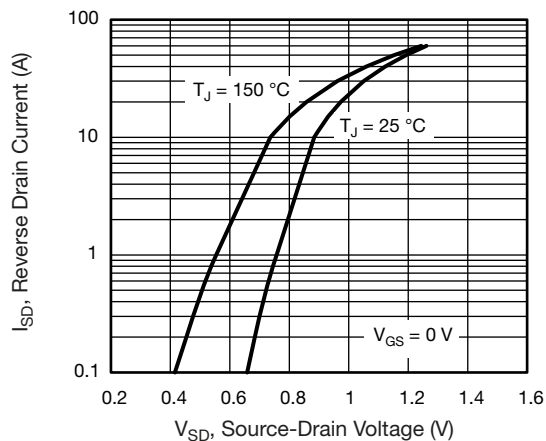
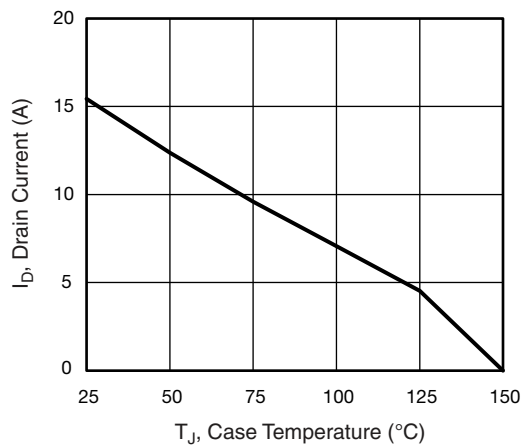
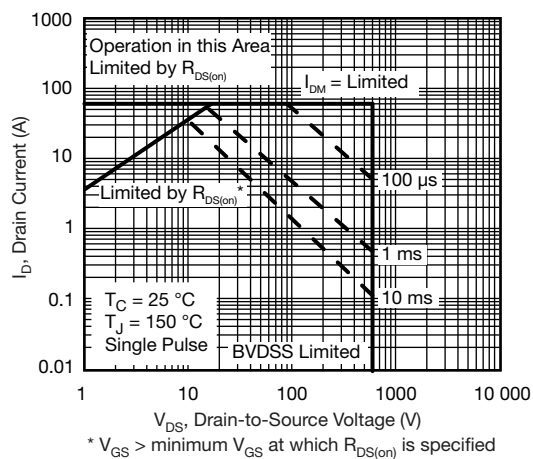
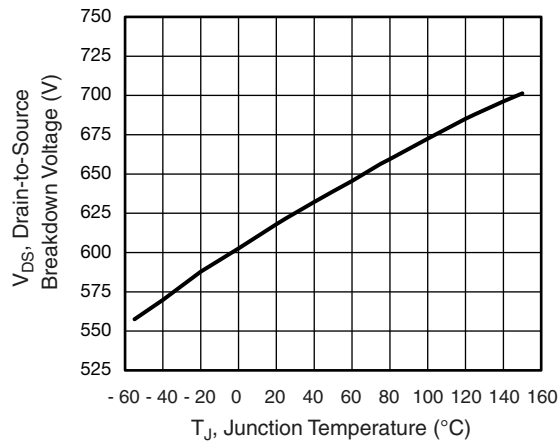
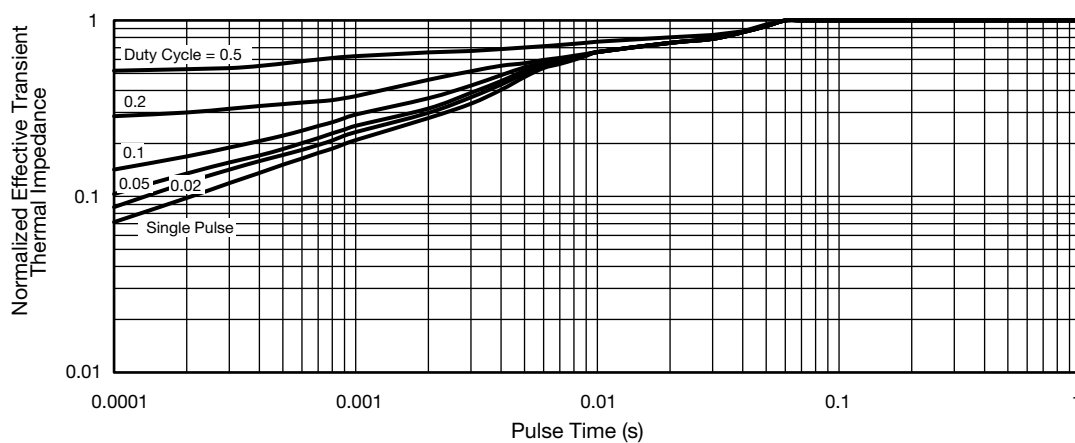
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

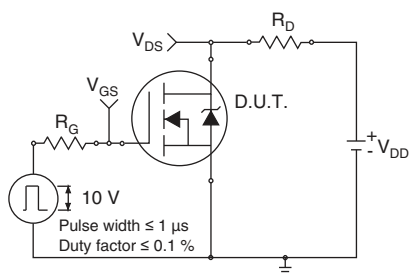
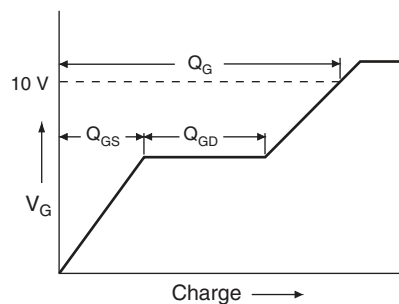
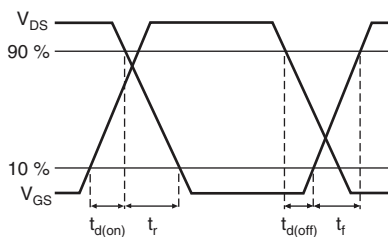
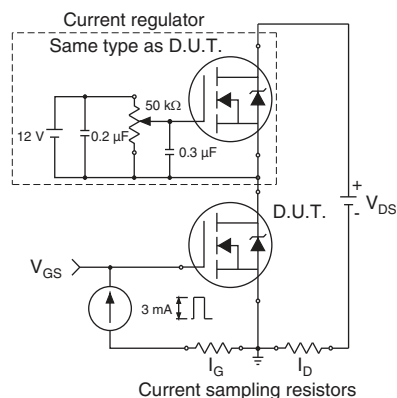
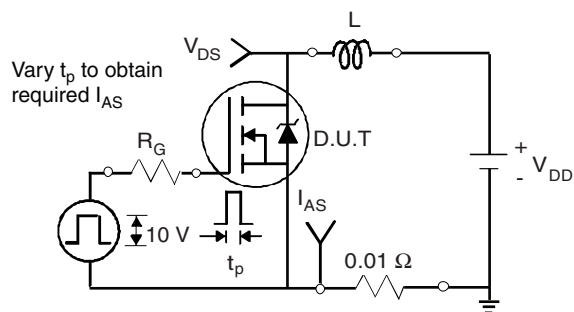
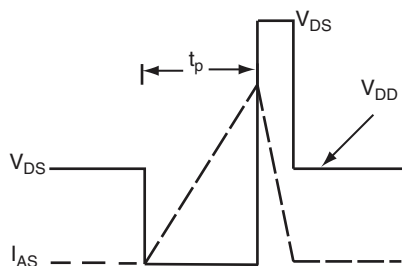
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		600	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.71	-	V/°C
Gate-Source Threshold Voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2	-	4	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V		-	-	1	μA
		V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	10	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 8 A	-	0.23	0.28	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 8 A		-	4.6	-	S
Dynamic							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V, f = 1 MHz		-	1350	-	pF
Output Capacitance	C <sub>oss</sub>			-	70	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	5	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	C <sub>o(er)</sub>	V <sub>DS</sub> = 0 V to 480 V, V <sub>GS</sub> = 0 V		-	53	-	
Effective Output Capacitance, Time Related <sup>b</sup>	C <sub>o(tr)</sub>			-	177	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 8 A, V <sub>DS</sub> = 480 V	-	39	78	nC
Gate-Source Charge	Q <sub>gs</sub>			-	11	-	
Gate-Drain Charge	Q <sub>gd</sub>			-	17	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 480 V, I <sub>D</sub> = 8 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 9.1 Ω		-	16	32	ns
Rise Time	t <sub>r</sub>			-	26	52	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	41	82	
Fall Time	t <sub>f</sub>			-	22	44	
Gate Input Resistance	R <sub>g</sub>	f = 1 MHz, open drain		-	0.86	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	15	A
Pulsed Diode Forward Current	I <sub>SM</sub>			-	-	60	
Diode Forward Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 8 A, V <sub>GS</sub> = 0 V		-	1.0	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> = 8 A, dI/dt = 100 A/μs, V <sub>R</sub> = 25 V		-	302	604	ns
Reverse Recovery Charge	Q <sub>rr</sub>			-	4.0	8	μC
Reverse Recovery Current	I <sub>RRM</sub>			-	24	-	A

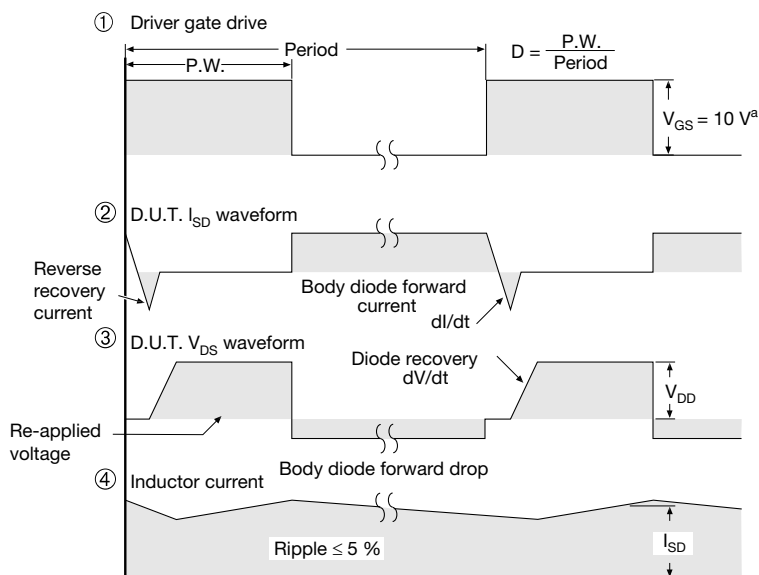
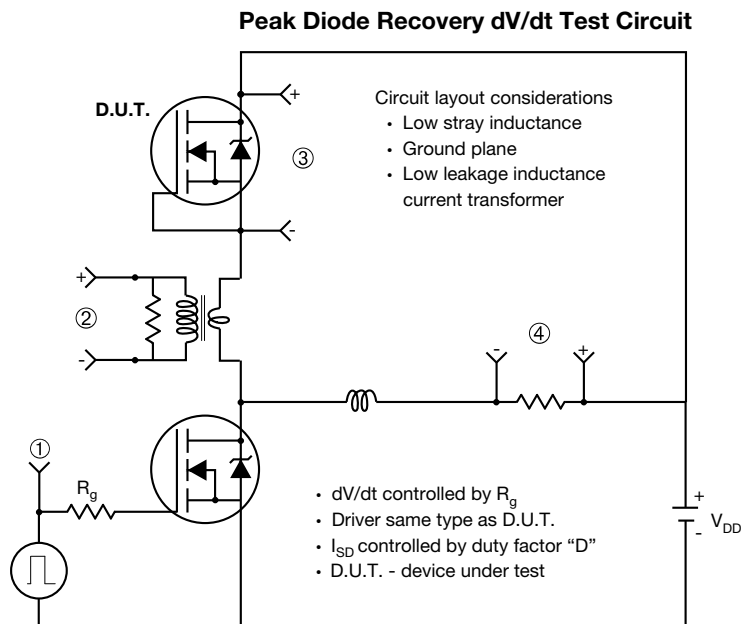
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Maximum Safe Operating Area**

**Fig. 10 - Temperature vs. Drain-to-Source Voltage**

**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**


**Fig. 12 - Switching Time Test Circuit**

**Fig. 16 - Basic Gate Charge Waveform**

**Fig. 13 - Switching Time Waveforms**

**Fig. 17 - Gate Charge Test Circuit**

**Fig. 14 - Unclamped Inductive Test Circuit**

**Fig. 15 - Unclamped Inductive Waveforms**

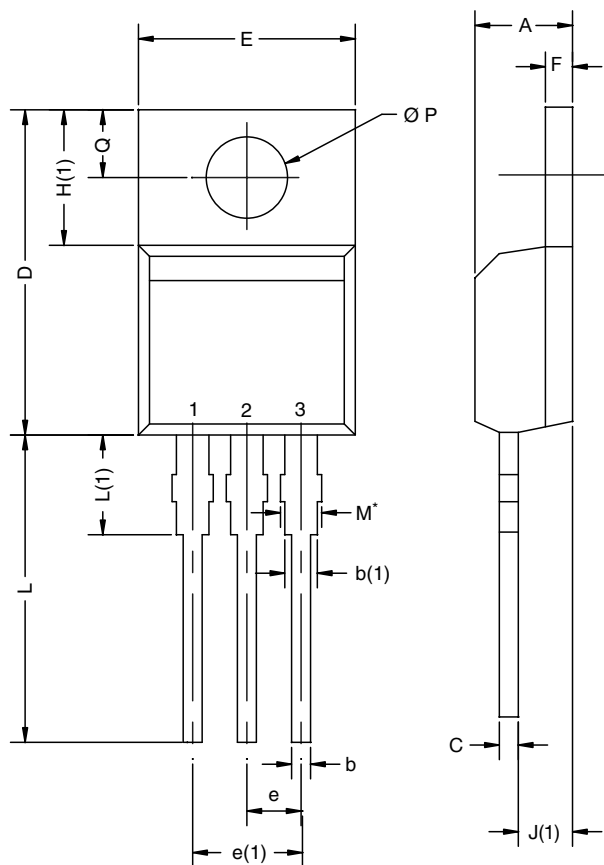


**Fig. 18 - For N-Channel**

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## TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T13-0724-Rev. O, 14-Oct-13  
DWG: 5471

### Note

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM



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